

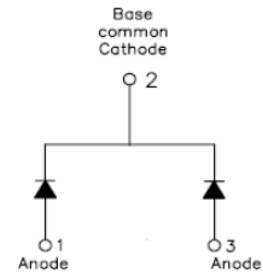
## SK20200C SCHOTTKY RECTIFIER

### Applications:

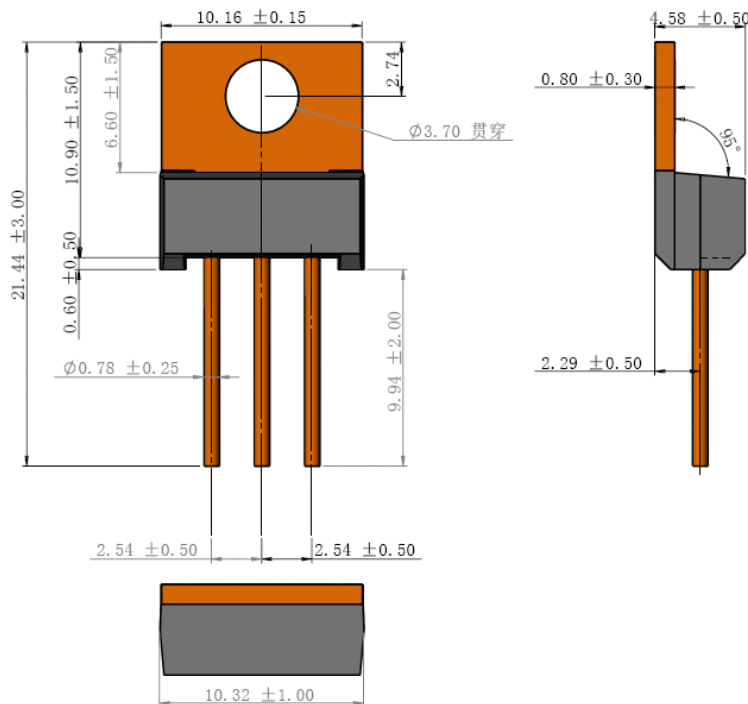
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Features:

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



### Mechanical Dimensions (In mm):



### TO-220AB



**Marking Diagram:**



Where XXXXX is YYWWL

SK = Device Type  
20 = Forward Current (20A)  
200 = Reverse Voltage (200V)  
C = Configuration  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
SK20200C	TO-220AB (Pb-Free)	50 pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	200	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C=105^\circ\text{C}$ , rectangular wave form	20	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	$I_{FSM}$	8.3 ms, half Sine pulse	150	A



**Electrical Characteristics:**

\*

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	$V_{F1}$	@ 10A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.90	V
	$V_{F2}$	@ 10A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.85	V
Max. Reverse Current (per leg) *	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.0	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	50	mA
Max. Junction Capacitance (per leg)	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25\text{ }^\circ\text{C}$ $f_{\text{SIG}} = 1\text{MHz}$	300	pF
Typical Series Inductance (per leg)	$L_S$	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ $\mu\text{s}$

Pulse Width < 300 $\mu\text{s}$ , Duty Cycle <2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	$T_J$	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	$T_{\text{stg}}$	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta\text{JC}}$	DC operation	4.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			

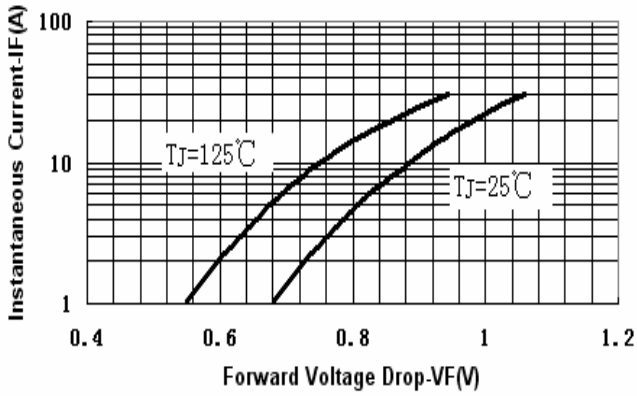


Fig.1-Typical Forward Voltage Drop Characteristics

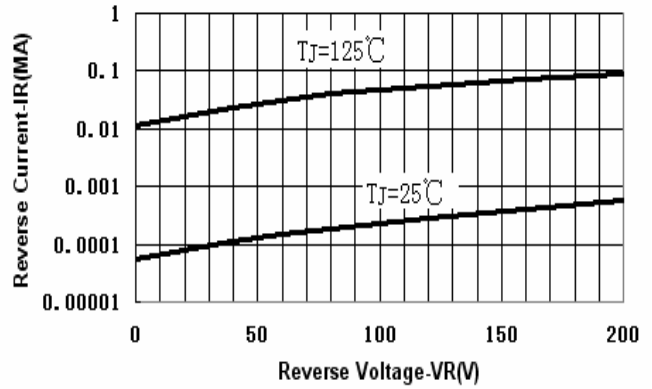


Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

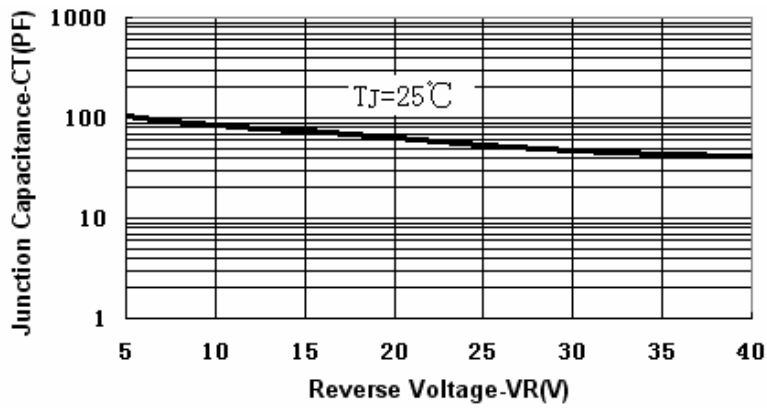


Fig.3-Typical Junction Capacitance Vs.Reverse Voltage



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